

AMENDMENTS TO THE SPECIFICATION

Please amend paragraph [0024], which begins on page 6, line 11, as follows:

[0024] Finally ~~(see FIG. 8)~~, the manufacturing of the n-MOSFET is further completed by deposition of a pre-metal dielectric, e.g. of silicon dioxide, followed by patterning thereof, deposition of a contact metal layer, e.g. of aluminum, again followed by patterning, resulting in the formation of contact regions. These steps are not shown in the drawings.